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(54) SUBSTRATE PROCESSING METHOD, METHOD OF MANUFACTURING SEMICONDUCTOR DEVICE, NON-TRANSITORY COMPUTER-READABLE RECORDING MEDIUM AND SUBSTRATE PROCESSING APPARATUS

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(57) ABSTRACT

There is provided a technique that includes: (a) adjusting a temperature of a substrate to a first temperature; (b) forming a first molybdenum-containing film on the substrate by performing: (b1) supplying a molybdenum-containing gas to the substrate; and (b2) supplying a reducing gas to the substrate for a first time duration; (c) adjusting the temperature of the substrate to a second temperature after performing (b); and (d) forming a second molybdenum-containing film on the first molybdenum-containing film by performing: (d1) supplying the molybdenum-containing gas to the substrate; and (d2) supplying the reducing gas to the substrate for a second time duration.

